Andreas D Wieck

List of Publications by Year in Descending Order

630 papers	11,722 citations	47 h-index	80 g-index
704 ext. papers	13,413 ext. citations	4.9 avg, IF	6.09 L-index

#	Paper	IF	Citations
630	Coulomb blockade: Toward charge control of self-assembled GaN quantum dots at room temperature. *Applied Physics Letters*, **2022**, 120, 012105	3.4	
629	Wafer-scale epitaxial modulation of quantum dot density.. *Nature Communications*, **2022**, 13, 1633	17.4	1
628	Formation of tungsten carbide by focused ion beam process: A route to high magnetic field resilient patterned superconducting nanostructures. *Applied Physics Letters*, **2022**, 120, 132601	3.4	0
627	Electron g-factor determined for quantum dot circuit fabricated from (110)-oriented GaAs quantum well. *Journal of Applied Physics*, **2022**, 131, 134305	2.5	
626	Analysing the entropy of lithium-ion cells to trace anodic half-cell ageing. *Journal of Energy Storage*, **2022**, 50, 104109	7.8	0
625	Dynamic measurement of the entropy coefficient for battery cells. *Journal of Energy Storage*, **2022**, 51, 104361	7.8	0
624	Full Wafer Property Control of Local Droplet Etched GaAs Quantum Dots. *Journal of Crystal Growth*, **2022**, 126713	1.6	0
623	Optically driving the radiative Auger transition. *Nature Communications*, **2021**, 12, 6575	17.4	2
622	Integrated Whispering-Gallery-Mode Resonator for Solid-State Coherent Quantum Photonics. *Nano Letters*, **2021**, 21, 8707-8714	11.5	1
621	Charge Tunable GaAs Quantum Dots in a Photonic n-i-p Diode. *Nanomaterials*, **2021**, 11,	5.4	3
620	Optical spin control and coherence properties of acceptor bound holes in strained GaAs. *Physical Review B*, **2021**, 103,	3.3	2
619	Electroabsorption in gated GaAs nanophotonic waveguides. *Applied Physics Letters*, **2021**, 118, 131106	3.4	2
618	Suppression of Surface-Related Loss in a Gated Semiconductor Microcavity. *Physical Review Applied*, **2021**, 15,	4.3	4
617	Suppression of nuclear spin fluctuations in an InGaAs quantum dot ensemble by GHz-pulsed optical excitation. *Npj Quantum Information*, **2021**, 7,	8.6	2
616	Probabilistic teleportation of a quantum dot spin qubit. *Npj Quantum Information*, **2021**, 7,	8.6	4
615	Tuning the Mode Splitting of a Semiconductor Microcavity with Uniaxial Stress. *Physical Review Applied*, **2021**, 15,	4.3	2
614	On the possible influence of the Fermi–Dirac statistics on the potential and entropy of galvanic cells. *Journal of Power Sources*, **2021**, 498, 229870	8.9	1

613	Distinguishing persistent effects in an undoped GaAs/AlGaAs quantum well by top-gate-dependent illumination. *Journal of Applied Physics*, **2021**, 129, 234301	2.5	1
612	Experimental Validation of Formula for Calculation Thermal Diffusivity in Superlattices Performed Using a Combination of Two Frequency-Domain Methods: Photothermal Infrared Radiometry and Thermoreflectance. *Applied Sciences (Switzerland)*, **2021**, 11, 6125	2.6	3
611	Coherent control of individual electron spins in a two-dimensional quantum dot array. *Nature Nanotechnology*, **2021**, 16, 296-301	28.7	13
610	Experimental Reconstruction of the Few-Photon Nonlinear Scattering Matrix from a Single Quantum Dot in a Nanophotonic Waveguide. *Physical Review Letters*, **2021**, 126, 023603	7.4	4
609	New signatures of the spin gap in quantum point contacts. *Nature Communications*, **2021**, 12, 5	17.4	4
608	Characterization of a surface plasmon antenna fabricated on a gate-defined lateral quantum dot. *Japanese Journal of Applied Physics*, **2021**, 60, SBBI01	1.4	0
607	Coherent Beam Splitting of Flying Electrons Driven by a Surface Acoustic Wave. *Physical Review Letters*, **2021**, 126, 070501	7.4	0
606	Distant spin entanglement via fast and coherent electron shuttling. *Nature Nanotechnology*, **2021**, 16, 570-575	28.7	7
605	Gate voltage dependence of noise distribution in radio-frequency reflectometry in gallium arsenide quantum dots. *Applied Physics Express*, **2021**, 14, 035002	2.4	
604	Quantum Sensor for Nanoscale Defect Characterization. *Physical Review Applied*, **2021**, 15,	4.3	2
603	Enhanced Spin Coherence while Displacing Electron in a Two-Dimensional Array of Quantum Dots. *PRX Quantum*, **2021**, 2,	6.1	2
602	In-flight distribution of an electron within a surface acoustic wave. *Applied Physics Letters*, **2021**, 119, 114004	3.4	1
601	Coherent Spin-Photon Interface with Waveguide Induced Cycling Transitions. *Physical Review Letters*, **2021**, 126, 013602	7.4	6
600	A bright and fast source of coherent single photons. *Nature Nanotechnology*, **2021**, 16, 399-403	28.7	76
599	Scalable integrated single-photon source. *Science Advances*, **2020**, 6,	14.3	42
598	Radiative Auger process in the single-photon limit. *Nature Nanotechnology*, **2020**, 15, 558-562	28.7	12
597	Characterization of low-resistance ohmic contacts to a two-dimensional electron gas in a GaAs/AlGaAs heterostructure. *EPJ Applied Physics*, **2020**, 89, 20101	1.1	
596	On-Chip Nanomechanical Filtering of Quantum-Dot Single-Photon Sources. *Laser and Photonics Reviews*, **2020**, 14, 1900404	8.3	6

595	Observation of the Kondo screening cloud. *Nature*, **2020**, 579, 210-213	50.4	14
594	Real-Time Detection of Single Auger Recombination Events in a Self-Assembled Quantum Dot. *Nano Letters*, **2020**, 20, 1631-1636	11.5	4
593	Electrostatic potential shape of gate-defined quantum point contacts. *Physical Review B*, **2020**, 101,	3.3	2
592	Microscopic model for the stacking-fault potential and the exciton wave function in GaAs. *Physical Review B*, **2020**, 101,	3.3	2
591	Coherence of a Driven Electron Spin Qubit Actively Decoupled from Quasistatic Noise. *Physical Review X*, **2020**, 10,	9.1	8
590	Full counting statistics of spin-flip and spin-conserving charge transitions in Pauli-spin blockade. *Physical Review Research*, **2020**, 2,	3.9	4
589	Suspended Spot-Size Converters for Scalable Single-Photon Devices. *Advanced Quantum Technologies*, **2020**, 3, 1900076	4.3	1
588	Detection and amplification of spin noise using scattered laser light in a quantum-dot microcavity. *Physical Review B*, **2020**, 101,	3.3	1
587	Lifetimes and Quantum Efficiencies of Quantum Dots Deterministically Positioned in Photonic-Crystal Waveguides. *Advanced Quantum Technologies*, **2020**, 3, 2000026	4.3	1
586	Influence of molecular beam effusion cell quality on optical and electrical properties of quantum dots and quantum wells. *Journal of Crystal Growth*, **2020**, 550, 125884	1.6	1
585	Measurement of Backaction from Electron Spins in a Gate-Defined GaAs Double Quantum dot Coupled to a Mesoscopic Nuclear Spin Bath. *Physical Review Letters*, **2020**, 125, 047701	7.4	3
584	Measurement of thermal transport properties of selected superlattice and thin films using frequency-domain photothermal infrared radiometry. *Measurement: Journal of the International Measurement Confederation*, **2020**, 166, 108226	4.6	7
583	Near Transform-Limited Quantum Dot Linewidths in a Broadband Photonic Crystal Waveguide. *ACS Photonics*, **2020**, 7, 2343-2349	6.3	12
582	Two-dimensional lateral surface superlattices in GaAs heterostructures with independent control of carrier density and modulation potential. *Applied Physics Letters*, **2020**, 117, 032102	3.4	1
581	On-chip deterministic operation of quantum dots in dual-mode waveguides for a plug-and-play single-photon source. *Nature Communications*, **2020**, 11, 3782	17.4	16
580	Spin-glass phase transition revealed in transport measurements. *Physical Review B*, **2020**, 102,	3.3	5
579	Deterministic positioning of nanophotonic waveguides around single self-assembled quantum dots. *APL Photonics*, **2020**, 5, 086101	5.2	9
578	Low-noise GaAs quantum dots for quantum photonics. *Nature Communications*, **2020**, 11, 4745	17.4	32

577	Closed-loop control of a GaAs-based singlet-triplet spin qubit with 99.5% gate fidelity and low leakage. *Nature Communications*, **2020**, 11, 4144	17.4	17
576	Excess noise in Al x Ga 1 kAs/GaAs based quantum rings. *Applied Physics Letters*, **2020**, 117, 063102	3.4	1
575	Two-dimensional electron bound hole photoluminescence in GaAs in perpendicular magnetic fields. *Semiconductor Science and Technology*, **2020**, 35, 085011	1.8	
574	Correlations between optical properties and Voronoi-cell area of quantum dots. *Physical Review B*, **2019**, 100,	3.3	8
573	Optical Detection of Single-Electron Tunneling into a Semiconductor Quantum Dot. *Physical Review Letters*, **2019**, 122, 247403	7.4	22
572	Contrast of 83% in reflection measurements on a single quantum dot. *Scientific Reports*, **2019**, 9, 8817	4.9	1
571	Ballistic rectification based on inhomogeneous magnetic stray fields. *Journal of Applied Physics*, **2019**, 125, 164304	2.5	
570	A machine learning approach for automated fine-tuning of semiconductor spin qubits. *Applied Physics Letters*, **2019**, 114, 133102	3.4	14
569	Quantum non-demolition measurement of an electron spin qubit. *Nature Nanotechnology*, **2019**, 14, 555-560	38.9	25
568	Coherent Optical Control of a Quantum-Dot Spin-Qubit in a Waveguide-Based Spin-Photon Interface. *Physical Review Applied*, **2019**, 11,	4.3	11
567	Difference in charge and spin dynamics in a quantum dot ead coupled system. *Physical Review B*, **2019**, 99,	3.3	2
566	Excitons in InGaAs quantum dots without electron wetting layer states. *Communications Physics*, **2019**, 2,	5.4	15
565	Temperature and bias anomalies in the photoluminescence of InAs quantum dots coupled to a Fermi reservoir. *Physical Review B*, **2019**, 99,	3.3	4
564	Angular momentum transfer from photon polarization to an electron spin in a gate-defined quantum dot. *Nature Communications*, **2019**, 10, 2991	17.4	18
563	Sound-driven single-electron transfer in a circuit of coupled quantum rails. *Nature Communications*, **2019**, 10, 4557	17.4	20
562	Nanomechanical single-photon routing. *Optica*, **2019**, 6, 524	8.6	25
561	Photogeneration of a single electron from a single Zeeman-resolved light-hole exciton with preserved angular momentum. *Physical Review B*, **2019**, 99,	3.3	6
560	A gated quantum dot strongly coupled to an optical microcavity. *Nature*, **2019**, 575, 622-627	50.4	81

559	Photon Noise Suppression by a Built-in Feedback Loop. *Nano Letters*, **2019**, 19, 135-141	11.5	2
558	Self-Organized Growth of Quantum Dots and Quantum Wires by Combination of Focused Ion Beams and Molecular Beam Epitaxy. *Physica Status Solidi (B): Basic Research*, **2019**, 256, 1800375	1.3	2
557	Luminescent NdS thin films: a new chemical vapour deposition route towards rare-earth sulphides. *Dalton Transactions*, **2019**, 48, 2926-2938	4.3	4
556	Quantum Optics with Near-Lifetime-Limited Quantum-Dot Transitions in a Nanophotonic Waveguide. *Nano Letters*, **2018**, 18, 1801-1806	11.5	35
555	Simultaneous measurement of thermal conductivity and diffusivity of an undoped Al 0.33 Ga 0.67 As thin film epitaxially grown on a heavily Zn doped GaAs using spectrally-resolved modulated photothermal infrared radiometry. *Thermochimica Acta*, **2018**, 662, 69-74	2.9	13
554	Detuning dependence of Rabi oscillations in an InAs self-assembled quantum dot ensemble. *Physical Review B*, **2018**, 97,	3.3	5
553	Illumination-induced nonequilibrium charge states in self-assembled quantum dots. *Physical Review B*, **2018**, 97,	3.3	3
552	Superresolution Microscopy of Single Rare-Earth Emitters in YAG and H3 Centers in Diamond. *Physical Review Letters*, **2018**, 120, 033903	7.4	6
551	Far-field nanoscopy on a semiconductor quantum dot via a rapid-adiabatic-passage-based switch. *Nature Photonics*, **2018**, 12, 68-72	33.9	10
550	Spin-photon interface and spin-controlled photon switching in a nanobeam waveguide. *Nature Nanotechnology*, **2018**, 13, 398-403	28.7	49
549	Unveiling the bosonic nature of an ultrashort few-electron pulse. *Nature Communications*, **2018**, 9, 2811	17.4	18
548	Decay and revival of electron spin polarization in an ensemble of (In,Ga)As quantum dots. *Physical Review B*, **2018**, 98,	3.3	7
547	Basic Requirements of Spin-Flip Raman Scattering on Excitonic Resonances and Its Modulation through Additional High-Energy Illumination in Semiconductor Heterostructures. *Physics of the Solid State*, **2018**, 60, 1611-1617	0.8	0
546	Dephasing of InAs quantum dot p-shell excitons studied using two-dimensional coherent spectroscopy. *Physical Review B*, **2018**, 98,	3.3	5
545	A fast quantum interface between different spin qubit encodings. *Nature Communications*, **2018**, 9, 5066	17.4	12
544	Interlayer charge transfer in n-modulation doped Al1⊠ Ga x As□GaAs single heterostructures. *Semiconductor Science and Technology*, **2018**, 33, 095020	1.8	1
543	Laplace deep level transient spectroscopy on self-assembled quantum dots. *Journal of Applied Physics*, **2018**, 124, 104301	2.5	0
542	Spin inertia of resident and photoexcited carriers in singly charged quantum dots. *Physical Review B* , **2018**, 98,	3.3	14

541	Theory of spin inertia in singly charged quantum dots. *Physical Review B*, **2018**, 98,	3.3	14
540	Four single-spin Rabi oscillations in a quadruple quantum dot. *Applied Physics Letters*, **2018**, 113, 093102	3.4	16
539	Coherent transfer of electron spin correlations assisted by dephasing noise. *Nature Communications*, **2018**, 9, 2133	17.4	24
538	Simultaneous measurement of infrared absorption coefficient of Carbon doped Al0.33Ga0.67As thin film and thermal boundary resistance between thin film and heavily Zn doped GaAs substrate using spectrally-resolved modulated photothermal infrared radiometry. *Thermochimica Acta*, **2018**, 667, 73-78	2.9	6
537	Coherent transmission of superconducting carriers through a ~2 nm polar semiconductor. *Superconductor Science and Technology*, **2018**, 31, 085007	3.1	9
536	Electron dynamics in transport and optical measurements of self-assembled quantum dots. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600625	1.3	4
535	Comparison of technologies for nano device prototyping with a special focus on ion beams: A review. *Applied Physics Reviews*, **2017**, 4, 011302	17.3	37
534	Classical information transfer between distant quantum dots using individual electrons in fast moving quantum dots. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600673	1.3	2
533	Synthesis and evaluation of new copper ketoiminate precursors for a facile and additive-free solution-based approach to nanoscale copper oxide thin films. *Dalton Transactions*, **2017**, 46, 2670-2679	4.3	15
532	Atomic/molecular layer deposition of hybrid inorganic–organic thin films from erbium guanidinate precursor. *Journal of Materials Science*, **2017**, 52, 6216-6224	4.3	13
531	Focused ion beam supported growth of monocrystalline wurtzite InAs nanowires grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2017**, 470, 46-50	1.6	2
530	In situ and operando observation of surface oxides during oxygen evolution reaction on copper. *Electrochimica Acta*, **2017**, 236, 104-115	6.7	21
529	Ion-induced interdiffusion of surface GaN quantum dots. *Nuclear Instruments & Methods in Physics Research B*, **2017**, 409, 107-110	1.2	
528	Ultra-low charge and spin noise in self-assembled quantum dots. *Journal of Crystal Growth*, **2017**, 477, 193-196	1.6	8
527	New amidinate complexes of indium(iii): promising CVD precursors for transparent and conductive InO thin films. *Dalton Transactions*, **2017**, 46, 10220-10231	4.3	18
526	A triangular triple quantum dot with tunable tunnel couplings. *Semiconductor Science and Technology*, **2017**, 32, 084004	1.8	16
525	On measurement of the thermal diffusivity of moderate and heavily doped semiconductor samples using modulated photothermal infrared radiometry. *Thermochimica Acta*, **2017**, 650, 33-38	2.9	15
524	On the infrared absorption coefficient measurement of thick heavily Zn doped GaAs using spectrally resolved modulated photothermal infrared radiometry. *Journal of Applied Physics*, **2017**, 122, 135109	2.5	14

523	Spin dynamics of quadrupole nuclei in InGaAs quantum dots. *Physical Review B*, **2017**, 95,	3.3	4
522	Indistinguishable and efficient single photons from a quantum dot in a planar nanobeam waveguide. *Physical Review B*, **2017**, 96,	3.3	65
521	All-electrical measurement of the triplet-singlet spin relaxation time in self-assembled quantum dots. *Applied Physics Letters*, **2017**, 111, 092103	3.4	2
520	Coherent and robust high-fidelity generation of a biexciton in a quantum dot by rapid adiabatic passage. *Physical Review B*, **2017**, 95,	3.3	25
519	Mesoscopic phase behavior in a quantum dot around crossover between single-level and multilevel transport regimes. *Physical Review B*, **2017**, 95,	3.3	5
518	Coherent long-distance displacement of individual electron spins. *Nature Communications*, **2017**, 8, 501	17.4	36
517	Higher-order spin and charge dynamics in a quantum dot-lead hybrid system. *Scientific Reports*, **2017**, 7, 12201	4.9	5
516	Positive centre voltage in T-branch junctions on n-type GaAs/AlGaAs based on hydrodynamics. *Semiconductor Science and Technology*, **2017**, 32, 105005	1.8	2
515	Demonstrating the decoupling regime of the electron-phonon interaction in a quantum dot using chirped optical excitation. *Physical Review B*, **2017**, 95,	3.3	17
514	Detection and Control of Spin-Orbit Interactions in a GaAs Hole Quantum Point Contact. *Physical Review Letters*, **2017**, 118, 146801	7.4	12
513	Efficiency enhancement of the coherent electron spin-flip Raman scattering through thermal phonons in (In,Ga)As/GaAs quantum dots. *Physical Review B*, **2017**, 95,	3.3	1
512	Single electron-photon pair creation from a single polarization-entangled photon pair. *Scientific Reports*, **2017**, 7, 16968	4.9	7
511	Non-universal transmission phase behaviour of a large quantum dot. *Nature Communications*, **2017**, 8, 1710	17.4	12
510	Low temperature growth of gallium oxide thin films via plasma enhanced atomic layer deposition. *Dalton Transactions*, **2017**, 46, 16551-16561	4.3	37
509	Conversion from Single Photon to Single Electron Spin Using Electrically Controllable Quantum Dots. *Journal of the Physical Society of Japan*, **2017**, 86, 011008	1.5	8
508	Narrow optical linewidths and spin pumping on charge-tunable close-to-surface self-assembled quantum dots in an ultrathin diode. *Physical Review B*, **2017**, 96,	3.3	18
507	A linear triple quantum dot system in isolated configuration. *Applied Physics Letters*, **2017**, 110, 233101	3.4	12
506	Robust Single-Shot Spin Measurement with 99.5% Fidelity in a Quantum Dot Array. *Physical Review Letters*, **2017**, 119, 017701	7.4	33

505	Nonequilibrium spin noise in a quantum dot ensemble. *Physical Review B*, **2017**, 95,	3.3	11
504	Mesoscopic Field-Effect-Induced Devices in Depleted Two-Dimensional Electron Systems. *Physical Review Applied*, **2017**, 8,	4.3	2
503	Two-dimensional coherent spectroscopy of a THz quantum cascade laser: observation of multiple harmonics. *Optics Express*, **2017**, 25, 21753-21761	3.3	7
502	Electro-optic routing of photons from a single quantum dot in photonic integrated circuits. *Optics Express*, **2017**, 25, 33514	3.3	16
501	Nanostrukturierung **2017**, 167-242		
500	Phase sensitive properties and coherent manipulation of a photonic crystal microcavity. *Optics Express*, **2016**, 24, 20672-84	3.3	
499	Giant permanent dipole moment of two-dimensional excitons bound to a single stacking fault. *Physical Review B*, **2016**, 94,	3.3	12
498	Stabilizing nuclear spins around semiconductor electrons via the interplay of optical coherent population trapping and dynamic nuclear polarization. *Physical Review B*, **2016**, 93,	3.3	4
497	Quantum Dephasing in a Gated GaAs Triple Quantum Dot due to Nonergodic Noise. *Physical Review Letters*, **2016**, 116, 046802	7.4	38
496	Optical Blocking of Electron Tunneling into a Single Self-Assembled Quantum Dot. *Physical Review Letters*, **2016**, 117, 017401	7.4	15
495	Decoupling a hole spin qubit from the nuclear´spins. *Nature Materials*, **2016**, 15, 981-6	27	45
494	Signatures of Hyperfine, Spin-Orbit, and Decoherence Effects in a Pauli Spin Blockade. *Physical Review Letters*, **2016**, 117, 206802	7.4	20
493	Single-electron Spin Resonance in a Quadruple Quantum Dot. *Scientific Reports*, **2016**, 6, 31820	4.9	18
492	Low-temperature behavior of transmission phase shift across a Kondo correlated quantum dot. *Physical Review B*, **2016**, 94,	3.3	7
491	Probing indirect exciton complexes in a quantum dot molecule via capacitance-voltage spectroscopy. *Physical Review B*, **2016**, 94,	3.3	3
490	Fast spin information transfer between distant quantum dots using individual electrons. *Nature Nanotechnology*, **2016**, 11, 672-6	28.7	52
489	Altering the luminescence properties of self-assembled quantum dots in GaAs by focused ion beam implantation. *Applied Physics B: Lasers and Optics*, **2016**, 122, 1	1.9	4
488	Nanoscale nonlinear effects in Erbium-implanted Yttrium Orthosilicate. *Journal of Luminescence*, **2016**, 177, 266-274	3.8	2

487	Advanced optical manipulation of carrier spins in (In,Ga)As quantum dots. *Applied Physics B: Lasers and Optics*, **2016**, 122, 1	1.9	3
486	Reconstruction of nuclear quadrupole interaction in (In,Ga)As/GaAs quantum dots observed by transmission electron microscopy. *Physical Review B*, **2016**, 93,	3.3	9
485	Electrical properties of carbon nanotubes/WS2 nanotubes (nanoparticles) hybrid films. *Nanosystems: Physics, Chemistry, Mathematics*, **2016**, 37-43	1.8	2
484	Thermal energy and charge currents in multi-terminal nanorings. *AIP Advances*, **2016**, 6, 065306	1.5	2
483	Thermal shift of the resonance between an electron gas and quantum dots: what is the origin?. *New Journal of Physics*, **2016**, 18, 123019	2.9	2
482	Broadband terahertz dispersion control in hybrid waveguides. *Optics Express*, **2016**, 24, 22319-33	3.3	7
481	Photoelectron generation and capture in the resonance fluorescence of a quantum dot. *Applied Physics Letters*, **2016**, 108, 263108	3.4	11
480	Role of the electron spin in determining the coherence of the nuclear spins in a quantum dot. *Nature Nanotechnology*, **2016**, 11, 885-889	28.7	23
479	Spatially indirect transitions in electric field tunable quantum dot diodes. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 437-441	1.3	3
478	Injection of a single electron from static to moving quantum dots. *Nanotechnology*, **2016**, 27, 214001	3.4	15
477	Development of yttrium alloy ion source and its application in nanofabrication. *Applied Physics A: Materials Science and Processing*, **2016**, 122, 1	2.6	1
476	Coherent electron-spin-resonance manipulation of three individual spins in a triple quantum dot. *Applied Physics Letters*, **2016**, 108, 153101	3.4	29
475	Production yield of rare-earth ions implanted into an optical crystal. *Applied Physics Letters*, **2016**, 108, 053108	3.4	16
474	Electric field distribution and exciton recombination line shape in GaAs. *Materials Research Express*, **2016**, 3, 056201	1.7	2
473	Polaron-induced lattice distortion of (In,Ga)As/GaAs quantum dots by optically excited carriers. *Nanotechnology*, **2016**, 27, 425702	3.4	6
472	Improving the Out-Coupling of a Metal-Metal Terahertz Frequency Quantum Cascade Laser Through Integration of a Hybrid Mode Section into the Waveguide. *Journal of Infrared, Millimeter, and Terahertz Waves*, **2016**, 37, 426-434	2.2	2
471	Auger Recombination in Self-Assembled Quantum Dots: Quenching and Broadening of the Charged Exciton Transition. *Nano Letters*, **2016**, 16, 3367-72	11.5	44
470	Coherent Control of the Exciton-Biexciton System in an InAs Self-Assembled Quantum Dot Ensemble. *Physical Review Letters*, **2016**, 117, 157402	7.4	25

469	Photoluminescence of gallium ion irradiated hexagonal and cubic GaN quantum dots. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 383, 1-5	1.2	3
468	Heat flow, transport and fluctuations in etched semiconductor quantum wire structures. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 571-581	1.6	2
467	Tuning the tunneling probability between low-dimensional electron systems by momentum matching. *Applied Physics Letters*, **2015**, 106, 243105	3.4	4
466	Influence of Post-Implantation Annealing Parameters on the Focused Ion Beam Directed Nucleation of InAs Quantum Dots. *Nano*, **2015**, 10, 1550049	1.1	1
465	Measurement of the transmission phase of an electron in a quantum two-path interferometer. *Applied Physics Letters*, **2015**, 107, 063101	3.4	11
464	Mode-selected heat flow through a one-dimensional waveguide network. *Applied Physics Letters*, **2015**, 106, 083102	3.4	8
463	Transform-limited single photons from a single quantum dot. *Nature Communications*, **2015**, 6, 8204	17.4	146
462	Electrically tunable hole g factor of an optically active quantum dot for fast spin rotations. *Physical Review B*, **2015**, 91,	3.3	27
461	All-Optical Preparation of Coherent Dark States of a Single Rare Earth Ion Spin in a Crystal. *Physical Review Letters*, **2015**, 115, 093602	7.4	33
460	Quantum Manipulation of Two-Electron Spin States in Isolated Double Quantum Dots. *Physical Review Letters*, **2015**, 115, 096801	7.4	43
459	Interplay of Electron and Nuclear Spin Noise in n-Type GaAs. *Physical Review Letters*, **2015**, 115, 176601	7.4	24
458	Nuclear spin polarization in the electron spin-flip Raman scattering of singly charged (In,Ga)As/GaAs quantum dots. *Physical Review B*, **2015**, 92,	3.3	3
457	Spectral modification of the laser emission of a terahertz quantum cascade laser induced by broad-band double pulse injection seeding. *Applied Physics Letters*, **2015**, 107, 111103	3.4	1
456	Fast probe of local electronic states in nanostructures utilizing a single-lead quantum dot. *Scientific Reports*, **2015**, 5, 14616	4.9	2
455	Photonic crystal cavities with metallic Schottky contacts. *Applied Physics Letters*, **2015**, 107, 041113	3.4	1
454	Ultrawide electrical tuning of light matter interaction in a high electron mobility transistor structure. *Scientific Reports*, **2015**, 5, 16812	4.9	3
453	New edge magnetoplasmon interference like photovoltage oscillations and their amplitude enhancement in the presence of an antidot lattice. *AIP Advances*, **2015**, 5, 117128	1.5	
452	Epitaxial lift-off for solid-state cavity quantum electrodynamics. *Journal of Applied Physics*, **2015**, 118, 075705	2.5	5

451	Optical properties of strain-compensated CdSe/ZnSe/(Zn,Mg)Se quantum well microdisks. *Optics Express*, **2015**, 23, 29079-88	3.3	3
450	Fabrication and characterisation of gallium arsenide ambipolar quantum point contacts. *Applied Physics Letters*, **2015**, 106, 183504	3.4	5
449	Robust population inversion by polarization selective pulsed excitation. *Scientific Reports*, **2015**, 5, 10313	4.9	2
448	Observation of time-resolved gain dynamics in a terahertz quantum cascade laser **2015**,		1
447	Magnetoconductance of a magnetic double barrier in a quantum wire. *Superlattices and Microstructures*, **2015**, 79, 54-62	2.8	
446	Extending the spectral range of CdSe/ZnSe quantum wells by strain engineering. *Physical Review B*, **2015**, 91,	3.3	6
445	Hybrid architecture for shallow accumulation mode AlGaAs/GaAs heterostructures with epitaxial gates. *Applied Physics Letters*, **2015**, 106, 012105	3.4	7
444	The effect of charged quantum dots on the mobility of a two-dimensional electron gas: How important is the Coulomb scattering?. *Journal of Applied Physics*, **2015**, 117, 054305	2.5	3
443	Rabi Oscillations in an InAs Quantum Dot Ensemble Observed in Pre-pulse 2D Coherent Spectroscopy. *Springer Proceedings in Physics*, **2015**, 271-274	0.2	
442	Direct quantitative electrical measurement of many-body interactions in exciton complexes in InAs quantum dots. *Physical Review Letters*, **2014**, 112, 046803	7.4	12
441	Electrical and optical properties of TiO2 thin films prepared by plasma-enhanced atomic layer deposition. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 416-424	1.6	34
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